

IGBT for Automotive Application

650 V, 50 A

AFGHL50T65RQDN

Using novel field stop IGBT technology, onsemi's new series of field stop 4th generation IGBTs offer the optimum performance for automotive applications. This technology is Short circuit rated and offers high figure of merit with low conduction and switching losses.

Features

- Maximum Junction Temperature: $T_J = 175^\circ\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operation
- High Current Capability
- Low Saturation Voltage: $V_{CE(Sat)} = 1.6\text{ V (Typ.) @ } I_C = 50\text{ A}$
- 100% of the Parts Tested for I_{LM} (Note 2)
- High Input Impedance
- Fast Switching
- Tightened Parameter Distribution
- AEC-Q101 Qualified
- This Device is Pb-Free and RoHS Compliant

Typical Applications

- E-compressor for HEV/EV, PTC Heater for HEV/EV

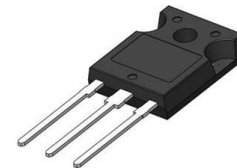
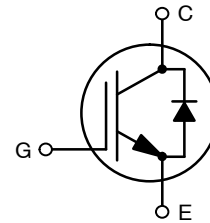
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-to-Emitter Voltage	V_{CES}	650	V
Gate-to-Emitter Voltage	V_{GES}	± 20	V
Transient Gate-to-Emitter Voltage		± 30	
Collector Current (Note 1) @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	I_C	78 50	A
Pulsed Collector Current (Note 2)	I_{LM}	200	A
Pulsed Collector Current (Note 3)	I_{CM}	200	A
Diode Forward Current (Note 1) @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	I_F	54 40	A
Pulsed Diode Maximum Forward Current	I_{FM}	160	A
Non-Repetitive Forward Surge Current (Half-Sine Pulse, $t_p = 8.3\text{ ms}$, $T_C = 25^\circ\text{C}$) (Half-Sine Pulse, $t_p = 8.3\text{ ms}$, $T_C = 50^\circ\text{C}$)	I_{FM}	160 140	A
Short Circuit Withstand Time $V_{GE} = 15\text{ V}$, $V_{CC} = 400\text{ V}$, $T_J \leq 150^\circ\text{C}$	t_{SC}	5	μs
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	P_D	346 173	W
Operating Junction/Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$
Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5 s	T_L	265	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Value limited by bond wire.
2. $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 200\text{ A}$, $R_G = 9\ \Omega$, Inductive Load, 100% Tested.
3. Repetitive Rating: pulse width limited by max. Junction temperature.

50 A, 650 V,
 $V_{CE(Sat)} = 1.6\text{ V (Typ.)}$



TO-247-3L
CASE 340CX

MARKING DIAGRAM



A = Assembly Site
 WW = Work Week Number
 Y = Year of Production, Last Number
 ZZ = Assembly Lot Number
 AFGHL50T65RQDN = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping
AFGHL50T65RQDN	TO-247-3L (Pb-Free)	30 Units / Rail

AFGHL50T65RQDN

THEMAL CHARACTERISTICS

Rating	Symbol	Min	Typ	Max	Unit
Thermal Resistance Junction-to-Case, for IGBT	$R_{\theta JC}$	-	0.33	0.43	°C/W
Thermal Resistance Junction-to-Case, for Diode	$R_{\theta JC}$	-	0.82	1.06	
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	-	-	40	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-emitter Breakdown Voltage, Gate-emitter Short-circuited	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	BV_{CES}	650	-	-	V
Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	$\frac{\Delta BV_{CES}}{\Delta T_J}$	-	0.6	-	V/°C
Collector-emitter Cut-off Current, Gate-emitter Short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	I_{CES}	-	-	30	μA
Gate Leakage Current, Collector-emitter Short-circuited	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	I_{GES}	-	-	±400	nA

ON CHARACTERISTICS

Gate-emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 50\text{ mA}$	$V_{GE(th)}$	3.2	5.0	6.0	V
Collector-emitter Saturation Voltage	$V_{GE} = 15\text{ V}, I_C = 50\text{ A}, T_J = 25^\circ\text{C}$ $V_{GE} = 15\text{ V}, I_C = 50\text{ A}, T_J = 175^\circ\text{C}$	$V_{CE(sat)}$	-	1.6	1.81	V
			-	1.9	-	

DYNAMIC CHARACTERISTICS

Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{ies}	-	2533	-	pF
Output Capacitance		C_{oes}	-	81	-	
Reverse Transfer Capacitance		C_{res}	-	11	-	
Gate Resistance	$f = 1\text{ MHz}$	R_g	-	15.06	-	Ω
Gate Charge Total	$V_{CC} = 400\text{ V}, I_C = 50\text{ A}, V_{GE} = 15\text{ V}$	Q_g	-	65	-	nC
Gate-Emitter Charge		Q_{ge}	-	19	-	
Gate-Collector Charge		Q_{gc}	-	18	-	

SWITCHING CHARACTERISTICS, INDUCTIVE LOAD

Turn-on Delay Time	$T_J = 25^\circ\text{C}, V_{CC} = 400\text{ V}, I_C = 25\text{ A}, R_G = 2.5\ \Omega, V_{GE} = 15\text{ V}, \text{ Inductive Load}$	$t_{d(on)}$	-	38	-	ns
Rise Time		t_r	-	23	-	
Turn-off Delay Time		$t_{d(off)}$	-	78	-	
Fall Time		t_f	-	82	-	
Turn-on Switching Loss		E_{on}	-	1.14	-	mJ
Turn-off Switching Loss		E_{off}	-	0.411	-	
Total Switching Loss		E_{ts}	-	1.58	-	
Turn-on Delay Time	$T_J = 25^\circ\text{C}, V_{CC} = 400\text{ V}, I_C = 50\text{ A}, R_G = 2.5\ \Omega, V_{GE} = 15\text{ V}, \text{ Inductive Load}$	$t_{d(on)}$	-	41	-	ns
Rise Time		t_r	-	40	-	
Turn-off Delay Time		$t_{d(off)}$	-	76	-	
Fall Time		t_f	-	64	-	
Turn-on Switching Loss		E_{on}	-	3.09	-	mJ
Turn-off Switching Loss		E_{off}	-	0.83	-	
Total Switching Loss		E_{ts}	-	3.92	-	

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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SWITCHING CHARACTERISTICS, INDUCTIVE LOAD

Turn-on Delay Time	$T_J = 175^\circ\text{C}$, $V_{CC} = 400\text{ V}$, $I_C = 25\text{ A}$, $R_G = 2.5\ \Omega$, $V_{GE} = 15\text{ V}$, Inductive Load	$t_{d(on)}$	-	38	-	ns
Rise Time		t_r	-	27	-	
Turn-off Delay Time		$t_{d(off)}$	-	92	-	
Fall Time		t_f	-	165	-	
Turn-on Switching Loss		E_{on}	-	1.26	-	mJ
Turn-off Switching Loss		E_{off}	-	0.99	-	
Total Switching Loss		E_{ts}	-	2.26	-	
Turn-on Delay Time	$T_J = 175^\circ\text{C}$, $V_{CC} = 400\text{ V}$, $I_C = 50\text{ A}$, $R_G = 2.5\ \Omega$, $V_{GE} = 15\text{ V}$, Inductive Load	$t_{d(on)}$	-	45	-	ns
Rise Time		t_r	-	46	-	
Turn-off Delay Time		$t_{d(off)}$	-	86	-	
Fall Time		t_f	-	133	-	
Turn-on Switching Loss		E_{on}	-	3.5	-	mJ
Turn-off Switching Loss		E_{off}	-	1.84	-	
Total Switching Loss		E_{ts}	-	5.34	-	

DIODE CHARACTERISTICS

Diode Forward Voltage	$I_F = 40\text{ A}$, $T_J = 25^\circ\text{C}$	V_F	-	1.65	2.20	V
	$I_F = 40\text{ A}$, $T_J = 175^\circ\text{C}$		-	1.7	-	

DIODE SWITCHING CHARACTERISTICS, INDUCTIVE LOAD

Reverse Recovery Energy	$I_F = 40\text{ A}$, $di_F/dt = 1000\text{ A}/\mu\text{s}$, $V_R = 400\text{ V}$, $T_J = 25^\circ\text{C}$	E_{rec}	-	43	-	μJ
Diode Reverse Recovery Time		T_{rr}	-	57	-	nS
Diode Reverse Recovery Charge		Q_{rr}	-	589	-	nC
Reverse Recovery Energy	$I_F = 40\text{ A}$, $di_F/dt = 1000\text{ A}/\mu\text{s}$, $V_R = 400\text{ V}$, $T_J = 175^\circ\text{C}$	E_{rec}	-	215	-	μJ
Diode Reverse Recovery Time		T_{rr}	-	118	-	nS
Diode Reverse Recovery Charge		Q_{rr}	-	1552	-	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS

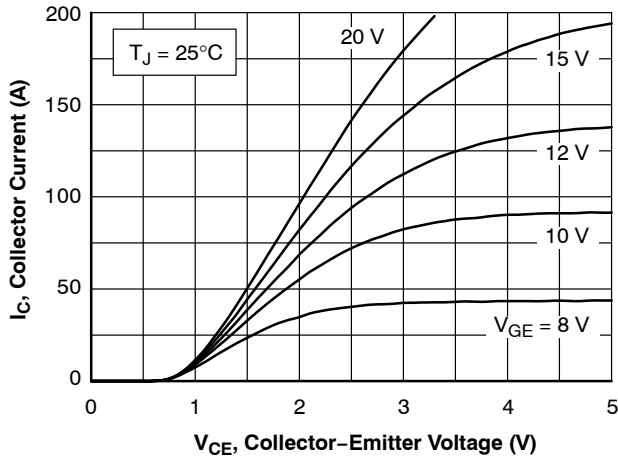


Figure 1. Typical Output Characteristics

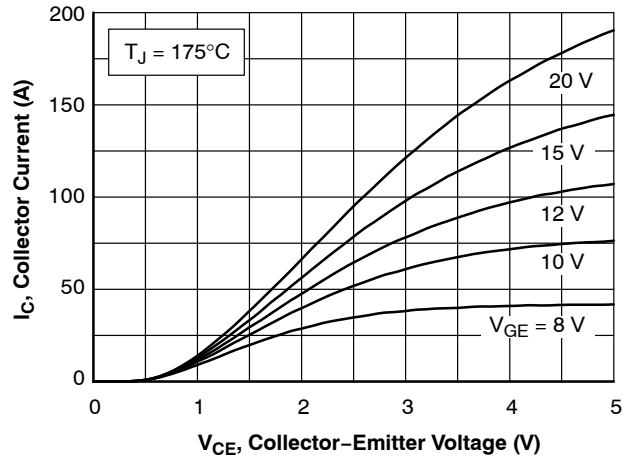


Figure 2. Typical Output Characteristics

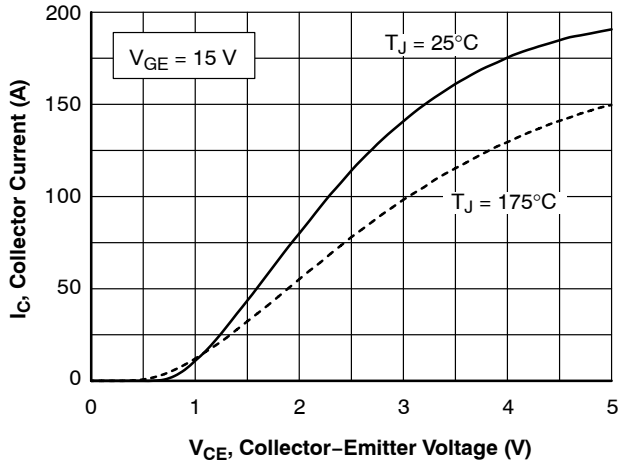


Figure 3. Typical Saturation Voltage Characteristics

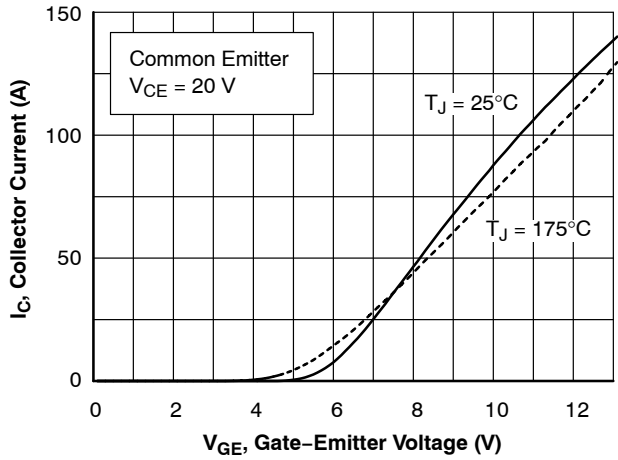


Figure 4. Typical Transfer Characteristics

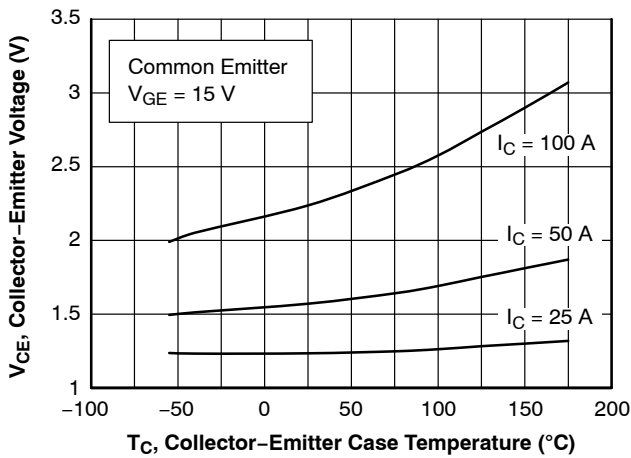


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

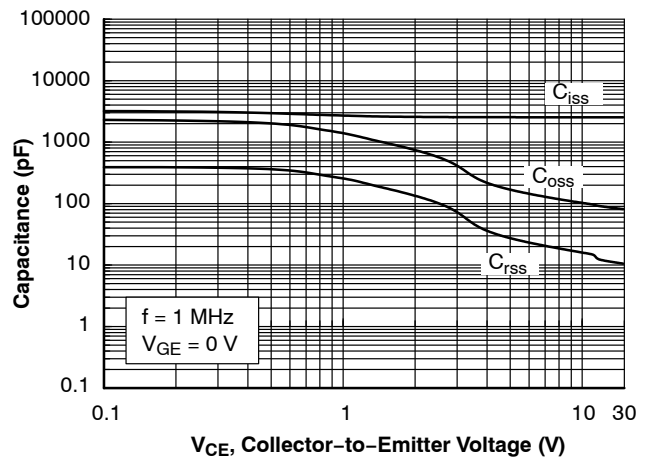


Figure 6. Capacitance Characteristics

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TYPICAL CHARACTERISTICS (Continued)

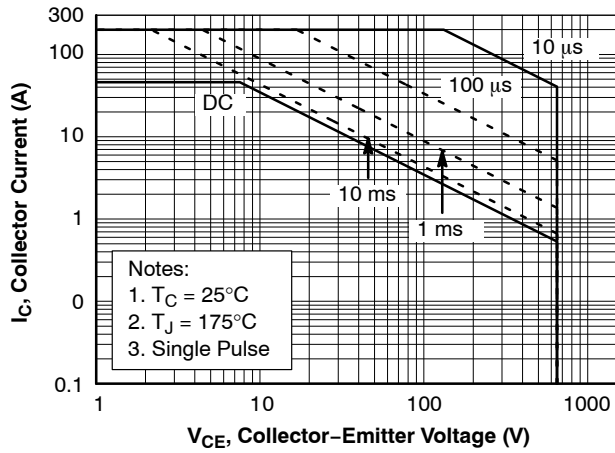


Figure 7. SOA Characteristics

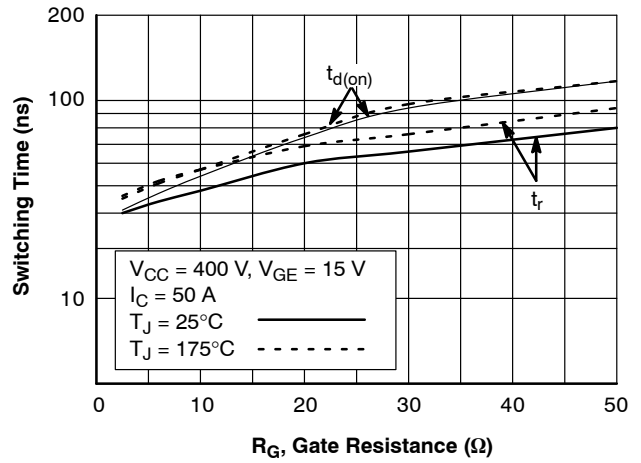


Figure 8. Turn-on Characteristics vs. Gate Resistance

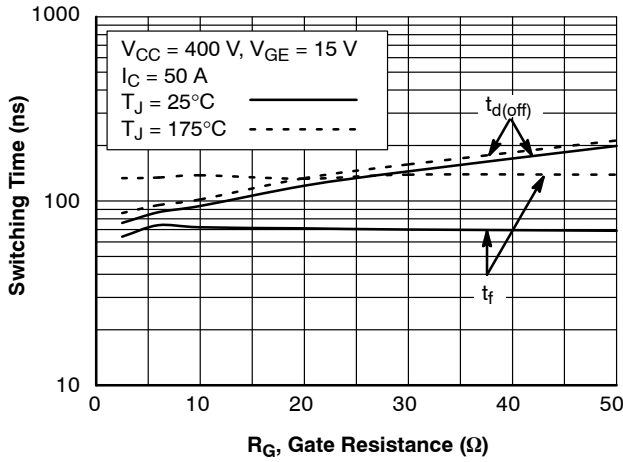


Figure 9. Turn-off Characteristics vs. Gate Resistance

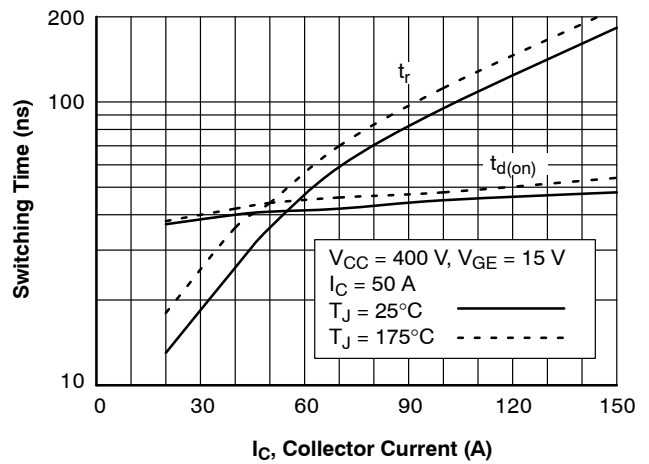


Figure 10. Turn-on Characteristics vs. Collector Current

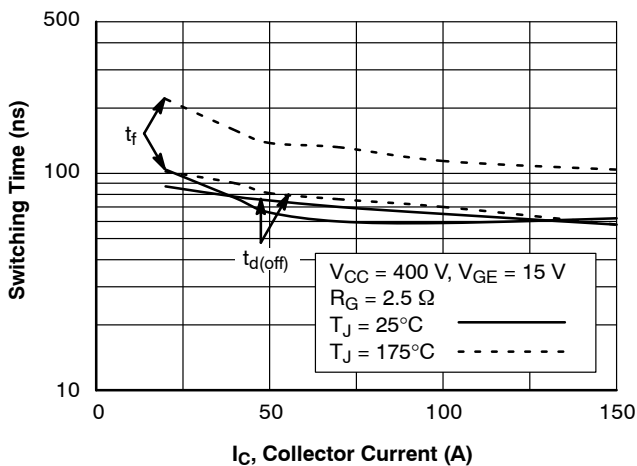


Figure 11. Turn-off Characteristics vs. Collector Current

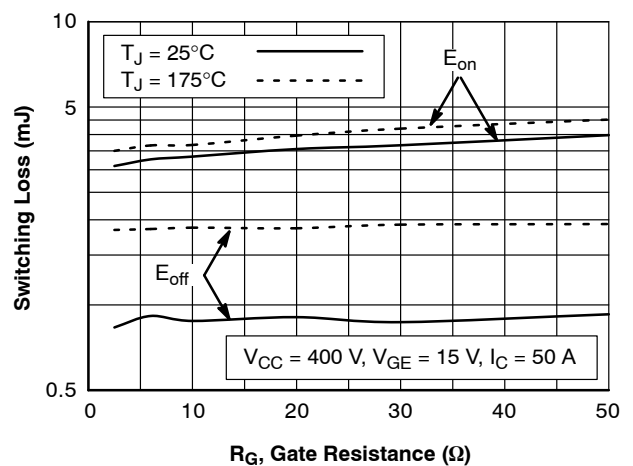


Figure 12. Switching Loss vs. Gate Resistance

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TYPICAL CHARACTERISTICS (Continued)

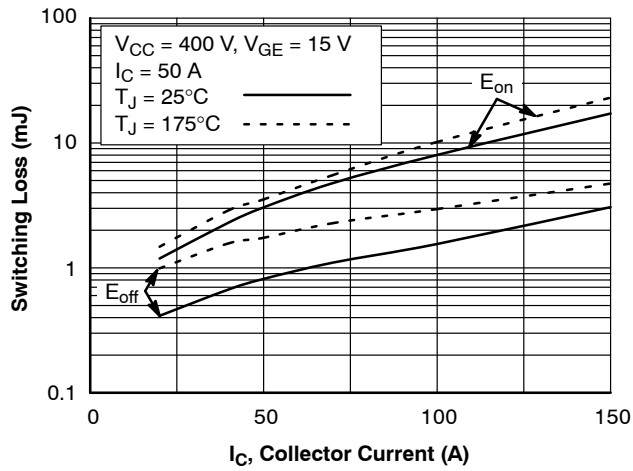


Figure 13. Switching Loss vs. Collector Current

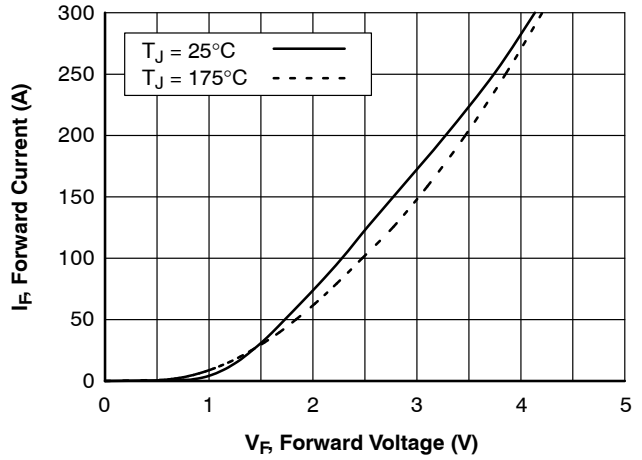


Figure 14. Forward Characteristics

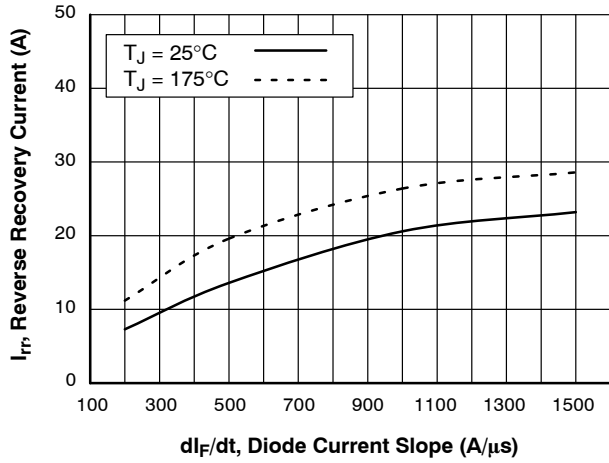


Figure 15. Reverse Recovery Current

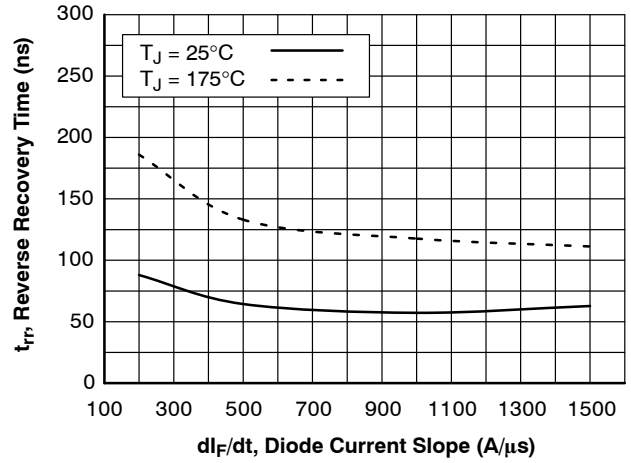


Figure 16. Reverse Recovery Time

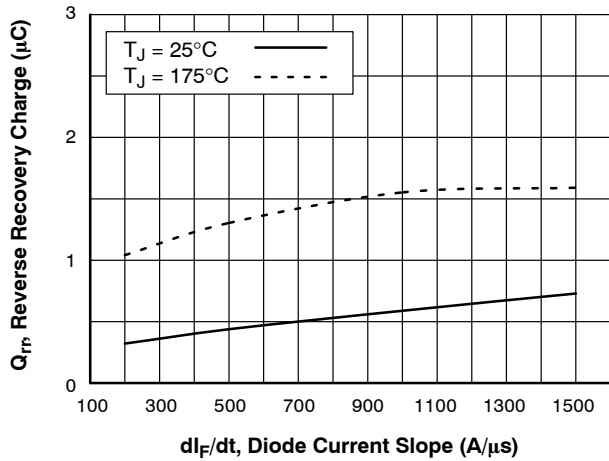


Figure 17. Stored Charge

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TYPICAL CHARACTERISTICS (Continued)

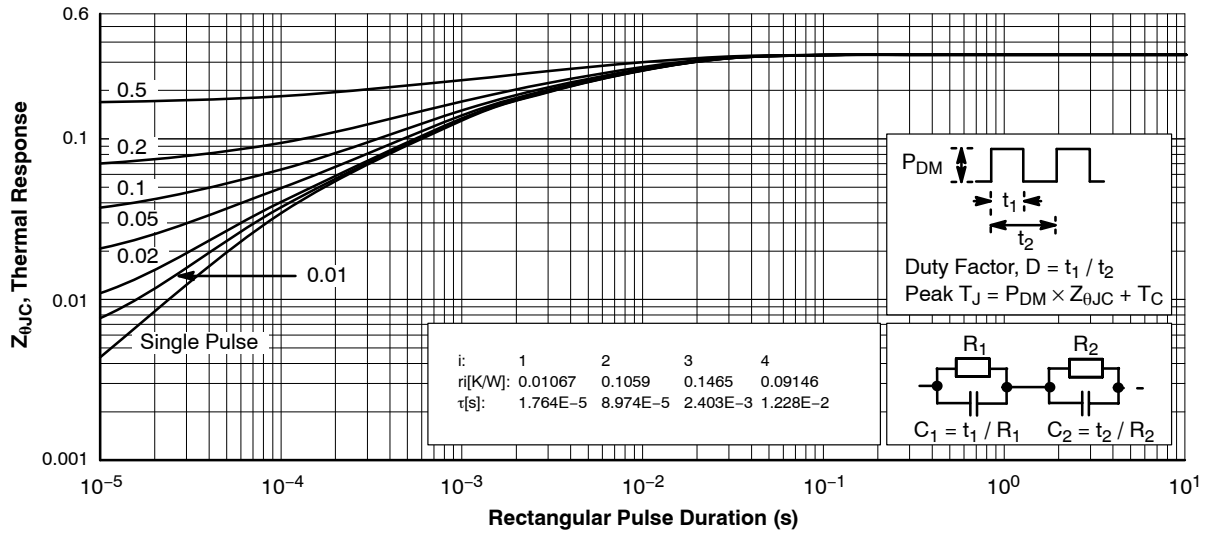


Figure 18. Transient Thermal Impedance of IGBT

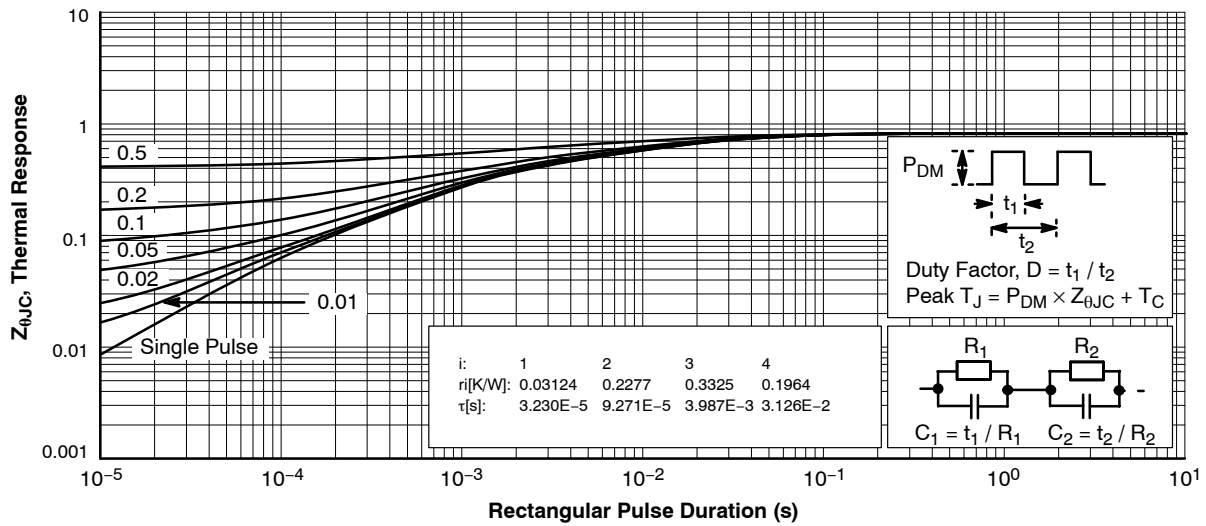
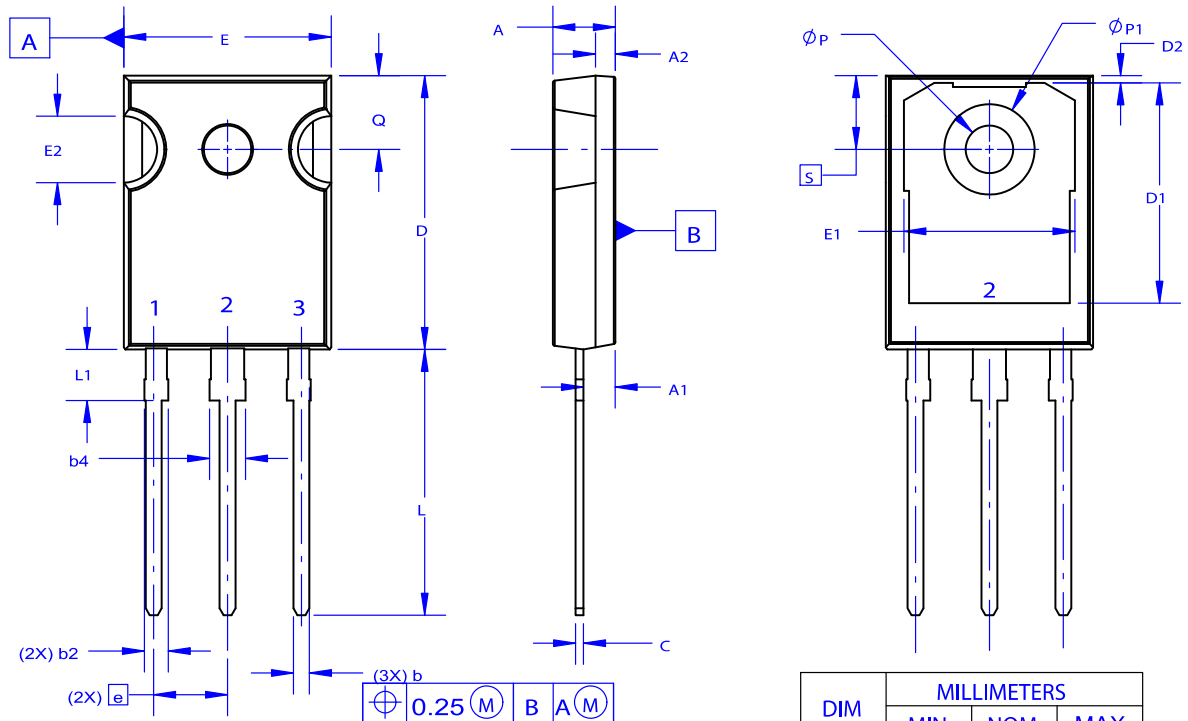


Figure 19. Transient Thermal Impedance of Diode

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PACKAGE DIMENSIONS

TO-247-3LD
CASE 340CX
ISSUE O



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ϕ P	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
ϕ P1	6.60	6.80	7.00

AFGHL50T65RQDN

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